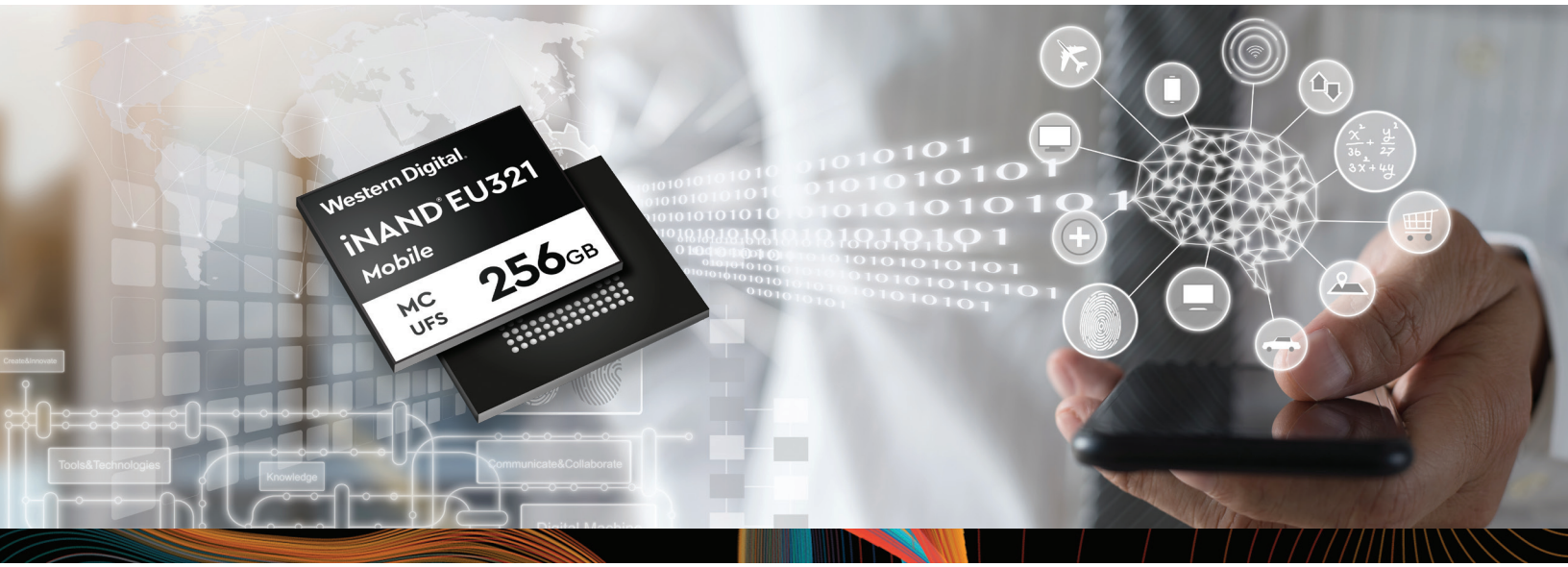
Western Digital. iNAND® MC EU321 Embedded Flash Drive

UFS 2.1 I 3D NAND I Superior Performance



UFS 2.1 embedded flash drive with industry-leading 96-Layer 3D NAND technology that effortlessly enables an exceptional user experience for data-centric mobile devices.

Innovations in photography, artificial intelligence and augmented reality for mobile devices ensure that these devices continue to remain the center of our digital lives. New smartphone camera capabilities are driven by artificial intelligence & machine learning techniques for image processing, increasing number of cameras on a device and greater megapixel densities. Artificial intelligence applications are now available even in mainstream devices with dedicated processors for image and speech recognition, as well as advanced photography capabilities. Augmented reality capabilities incorporated into the OS are enabling applications to converge the physical and digital worlds.

Western Digital iNAND® MC EU321 EFD, using industry leading 96-Layer 3D NAND technology, effortlessly enables an exceptional user experience for data-centric smartphones and mobile devices. Applications such as 4K video, slow motion video, high resolution photography, augmented reality, virtual reality, and AI can quickly fill the storage on a device. A device with near full storage will typically experience degraded performance, thereby resulting in an inferior user experience. The iNAND EU321 with iNAND® SmartSLC 5.1 is designed to maintain high and persistent performance even as the device approaches full capacity. Combined with superior and persistent write speeds, the iNAND EU321 enables consumers to create, enjoy and preserve their digital moments.

Specifications

Capacity[2]	Package Size	UFS Version	Part Number	UFS Specification
32GB	11.5×13×1.0mm	V2.1 HS-G3	SDINDDC4-32G	2.1
64GB	11.5×13×1.0mm	V2.1 HS-G3	SDINDDC4-64G	2.1
128GB	11.5×13×1.0mm	V2.1 HS-G3	SDINDDC4-128G	2.1
256GB	11.5×13×1.0mm	V2.1 HS-G3	SDINDDC4-256G	2.1

[1] Compatible with Android™, Chrome, and Windows® mobile operating systems.
[2] 1 GB = 1,000,000,000 bytes. Actual user capacity less.

Key Benefits

Performance

- iNAND® SmartSLC 5.1 technology provides an exceptional user experience by maintaining high SLC (Single Level Cell) performance as the device approaches its maximum storage capacity by utilizing the SLC buffer to clean up fragmented data during idle time between bursts.
- Leading sequential write performance with a 10% improvement over prior generation utilizing iNAND® SmartSLC 5.1 technology optimized for high-resolution photography, fast file transfer and content download.

Design

- Industry-leading 96-Layer 3D NAND
- Full vertical integration: UFS controller, 3D NAND technology, firmware, assembly and test, designed and developed by Western Digital.
- UFS 2.1 coupled with 96-Layer 3D NAND technology delivers an energy-efficient storage solution, superior sequential write speeds and high capacities for mobile devices.
- Capacities from 32GB to 256GB in a small form factor allow for scalability and design flexibility.

Main Features

- UFS 2.1 Gear3 2-Lane
- iNAND® SmartSLC 5.1 technology
- Plug-and-Play integration
- Field Firmware Upgrade (FFU)
- Multiple RPMB regions
- Secure Write Protection
- Health and diagnostic reporting
- Production State Awareness

Contact Information

For all inquiries, please email:
OEMProducts@WDC.com

For more information, please visit:
www.WesternDigital.com

Western Digital Corporation | 5601 Great Oaks Parkway | San Jose | CA 95119 | USA

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